

Description

The IRF530NPBF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-220C (TO-220AB)

General Features

V_{DS} = 100V l_D =17A

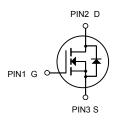
 $R_{DS(ON)}$ < 120m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Units Tube
IRFZ44NPBF	TO-220C(TO-220AB)	HXY MOSFET	50

Absolute Maximum Ratings (T_C=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	100	V
Vgs	Gate-Source Voltage ±20		V
ID	Continuous Drain CurrentTC=25 °C	17	А
ID	Continuous Drain CurrentTC=100°C	8	Α
IDM	Pulsed Drain Current note1	50	A
EAS	Single Pulse Avalanche Energy ³	250	mJ
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Reja	Thermal Resistance Junction-Ambient ¹ 62.5		°C/W
Rejc	Thermal Resistance Junction-Ambient ¹	1.42	°C/W

N-Channel Enhancement Mode MOSFET

Electrical Characteristics (Tc=25°C unless otherwise specified)

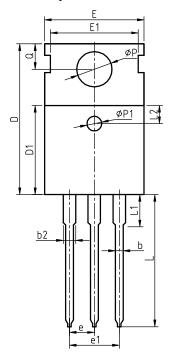
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _G s=0V,I _D =250µA	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V_{DS} =100V, V_{GS} = 0V, T_{J} = 25°C			5	μΑ
Igss	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250µA	1.5	2.0	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =8A	80		120	mΩ
C _{iss}	Input Capacitance	\/ OF\/ \/ O\/		1331		pF
Coss	Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$		276		pF
Crss	Reverse Transfer Capacitance	f = 1.0MHz		88		pF
Qg	Total Gate Charge	\/ 00\/ L 40A		53		nC
Qgs	Gate-Source Charge	$V_{DD} = 80V, I_{D} = 18A,$ $V_{GS} = 10V$		6		nC
Q_{gd}	Gate-Drain("Miller") Charge	VGS = 10V		29		nC
t _{d(on)}	Turn-on Delay Time			35		ns
tr	Turn-on Rise Time	$V_{DD} = 50V, I_D = 18A,$		45		ns
t _{d(off)}	Turn-off Delay Time	$R_G = 25\Omega$		187		ns
tf	Turn-off Fall Time			64		ns
Is	Maximum Continuous Drain to Source Diode Forward Current				18	Α
Ism	Maximum Pulsed Drain to Source Diode Forward Current				50	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} =18A			2	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =18A,		102		ns
Qrr	Reverse Recovery Charge	di/dt=100A/µs		0.5		μC

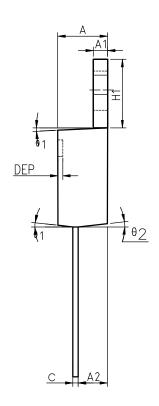
Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

- 2. I_{AS}=15A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25°C
- 3. Pulse Test: Pulse Width≤325µs, Duty Cycle≤1%

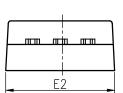


Package Information TO-220C(TO-220AB)





COMMON DIMENSIONS



SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
Α	4.40	4.57	4.70	0.173	0.180	0.185
A1	1. 27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1. 17	1. 27	1.36	0.046	0.050	0.054
С	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9. 10	9. 20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
Е	9.80	10.00	10.20	0. 386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
е		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0. 252	0.256	0. 260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
Р	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
θ 1	5°	7°	9°	5°	7°	9°
θ 2	1°	3°	5°	1°	3°	5°
θ 3	1°	3°	5°	1°	3°	5°



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